Driver Transistor

PNP Silicon

Features

- Moisture Sensitivity Level: 1
- ESD Rating:
 - ◆ Human Body Model 4 kV
 - ♦ Machine Model 400 V
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	-80	Vdc
Collector-Base Voltage	V _{CBO}	-80	Vdc
Emitter-Base Voltage	V _{EBO}	-4.0	Vdc
Collector Current – Continuous	I _C	-500	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board T _A = 25°C	P _D	460	mW
Thermal Resistance, Junction to Ambient (Note 1)	$R_{\theta JA}$	272	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

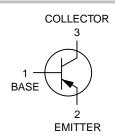


ON Semiconductor®

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SC-70 (SOT-323) CASE 419 STYLE 3



MARKING DIAGRAM



FM = Device Code
M = Date Code*

Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBTA56WT1G	SC-70 (Pb-Free)	3,000 / Tape & Reel
SMMBTA56WT1G	SC-70 (Pb-Free)	3,000 / Tape & Reel
SMMBTA56WT3G	SC-70 (Pb-Free)	10,000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{1.} FR-4 Board, 1 oz. Cu, 100 mm².

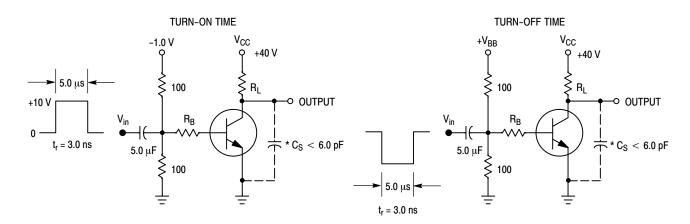
^{*}Date Code orientation may vary depending upon manufacturing location.

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	,			•
Collector–Emitter Breakdown Voltage (Note 1) (I _C = -1.0 mAdc, I _B = 0)	V _(BR) CEO	-80	_	Vdc
Emitter-Base Breakdown Voltage $(I_E = -100 \mu Adc, I_C = 0)$	V _{(BR)EBO}	-4.0	-	Vdc
Collector Cutoff Current (V _{CE} = -60 Vdc, I _B = 0)	I _{CES}	-	-0.1	μAdc
Collector Cutoff Current $(V_{CB} = -60 \text{ Vdc}, I_E = 0)$ $(V_{CB} = -80 \text{ Vdc}, I_E = 0)$	Ісво	- -	_ _0.1	μAdc
ON CHARACTERISTICS				
DC Current Gain ($I_C = -10 \text{ mAdc}$, $V_{CE} = -1.0 \text{ Vdc}$) ($I_C = -100 \text{ mAdc}$, $V_{CE} = -1.0 \text{ Vdc}$)	h _{FE}	100 100		-
Collector–Emitter Saturation Voltage ($I_C = -100 \text{ mAdc}$, $I_B = -10 \text{ mAdc}$)	V _{CE(sat)}	-	-0.25	Vdc
Base-Emitter On Voltage ($I_C = -100 \text{ mAdc}$, $V_{CE} = -1.0 \text{ Vdc}$)	V _{BE(on)}	-	-1.2	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current-Gain - Bandwidth Product (Note 2) (I _C = -100 mAdc, V _{CE} = -1.0 Vdc, f = 100 MHz)	f _T	50	_	MHz

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 1. Pulse Test: Pulse Width $\leq 300 \ \mu s$, Duty Cycle $\leq 2.0\%$.



*Total Shunt Capacitance of Test Jig and Connectors For PNP Test Circuits, Reverse All Voltage Polarities

Figure 1. Switching Time Test Circuits

^{2.} f_T is defined as the frequency at which |h_{fe}| extrapolates to unity.

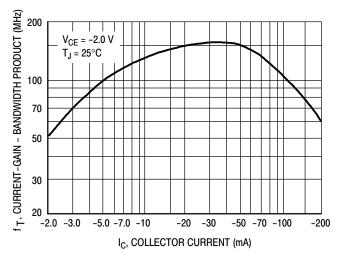


Figure 2. Current-Gain — Bandwidth Product

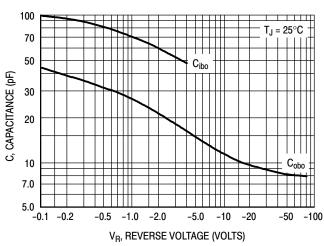


Figure 3. Capacitance

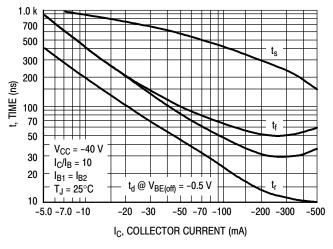


Figure 4. Switching Time

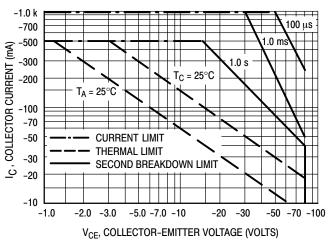


Figure 5. Active-Region Safe Operating Area

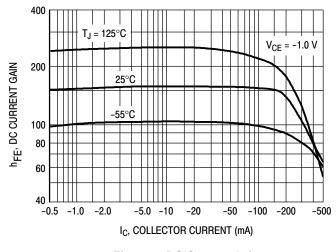


Figure 6. DC Current Gain

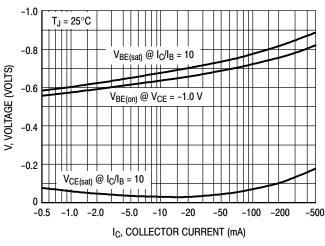


Figure 7. "ON" Voltages

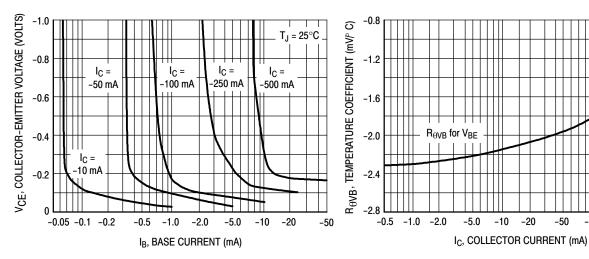


Figure 8. Collector Saturation Region

Figure 9. Base-Emitter Temperature Coefficient

-20

-200

-500

-100





SC-70 (SOT-323) **CASE 419** ISSUE R

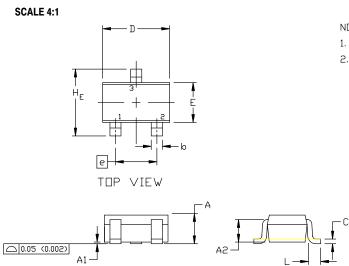
END VIEW

DATE 11 OCT 2022

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH

	MILLIMETERS			INCHES			
	MILLIMETERS				INCHES		
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.	
Α	0.80	0.90	1.00	0.032	0.035	0.040	
A1	0.00	0.05	0.10	0.000	0.002	0.004	
A2		0.70 REF			0.028 BSC		
b	0.30	0.35	0.40	0.012	0.014	0.016	
С	0.10	0.18	0.25	0.004	0.007	0.010	
D	1.80	2.00	2.20	0.071	0.080	0.087	
E	1.15	1.24	1.35	0.045	0.049	0.053	
е	1.20	1.30	1.40	0.047	0.051	0.055	
e1	0.65 BSC			0.026 BS	C		
L	0.20	0.38	0.56	0.008	0.015	0.022	
HE	2.00	2.10	2.40	0.079	0.083	0.095	



GENERIC MARKING DIAGRAM

SIDE VIEW

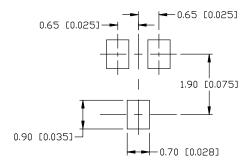


= Specific Device Code XX

Μ = Date Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.



For additional information on our Pb-Free strategy and soldering details, please download the ID Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

SOLDERING FOOTPRINT

STYLE 1: CANCELLED	STYLE 2: PIN 1. ANODE 2. N.C. 3. CATHODE	STYLE 3: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. CATHODE	
STYLE 6:	STYLE 7:	STYLE 8:	STYLE 9:	STYLE 10:	STYLE 11:
PIN 1. EMITTER	PIN 1. BASE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. CATHODE
2. BASE	2. EMITTER	2. SOURCE	2. CATHODE	2. ANODE	CATHODE
COLLECTOR	COLLECTOR	3. DRAIN	CATHODE-ANODE	3. ANODE-CATHODE	CATHODE

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DESCRIPTION:	SC-70 (SOT-323)		PAGE 1 OF 1	

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